A Cached VRAM for 3D Graphics

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Motivation

 Existing RAMs are too slow for Z-buffered rendering
 DRAM: best bit density
 VRAM: improved bandwidth
 Massive Interleaving: expensive
 SRAM: fast cycle time; expensive
 Exotics: optimized for large polygons

Key Design Concepts

- Convert read-modify-write cycles into write only operations
- Two levels of internal rectangular pixel caches
- Leverage Existing 16Mbit DRAM technology
 - Use standard DRAM process Use standard circuit designs Use standard DRAM die size

Read-Modify-Write Interface

Used by Z-buffering & RGB Blending

- 1. Read old pixel & receive new pixel
- 2. Merge new and old pixels; turn bus
- 3. Write merged pixel
- 4. Turn bus again

Traditional RMW Frame Buffer Interface



3D RAM Write Only Interface

- 3D RAM removes the bidirectional pin interface bottleneck
- Move RMW cycle inside 3D RAM
- Z-buffering done inside 3D RAM
- Internal ALU merges new and old pixels
- External interface is write only

3D RAM Write Only Interface

- ALU operations are pipelined
- All reads, writes, and processing overlapped @ 10ns/pixel rate
- No bus turn around required
- 100 Million pixels/sec per chip!

3DRAM Write Only Interface



Conditional Write



On-chip Caching System

- Rectangular blocks for graphics Near-isotropic performance
- Two levels of cache

L1\$ small, fast, multiported SRAM L2\$ big, slow, multiported buffer

Multiple DRAM banks

Hide DRAM access & precharge

On-chip Caching System



L1 Cache

- 3 port SRAM
 - 10 ns 32 bit read port to Pixel ALU 10 ns 32 bit write port from Pixel ALU 20 ns 256 bit bidirectional to global bus
- Eight 256 bit blocks
- Writeback
- N-way associativity

Global Bus

- Connects L1\$ to L2\$
- One L1\$ block wide
- Transfers 256 bits in 20 ns
- Bidirectional L1\$⇔L2\$
- L1\$⇒L2\$ transfers are plane and byte maskable

L2 Cache

- Four 10,240 bit page buffers
- Each buffer has 3 ports
 20 ns 256 bit to global bus
 40 ns 640 bit to video buffer
 120 ns 10,240 bit to DRAM
- Write through
- Direct mapped

DRAM Banks

- 4 independent banks
- 256 pages per bank
- 10,240 bits per page
- •10 Mb per chip

Fast Fills

- Must clear the screen before rendering each frame
- Fast constant color rectangle fill
- Worth accelerating in hardware
- Uses existing busses

Video Port

- Frees random access port for rendering
- Two 20 pixel shift registers Inexpensive; small die area ping pong: seamless video
- Frequent reloads (~600 ns)



Typical Frame Buffer Organization



12 chip system; 1280x1024; double buffer + Z

Performance

Triangles	50 pixel	2-4M /sec
	100 pixel	1.5-1.8M /sec
Vectors	10 pixel	3.5-7.5M /sec
Fast Clear	Block Fill	1.2-1.6G pixel/sec
	Page Fill	24-32G pixel/sec
Image Copy	Write	264-400M pixel/sec
	Read	132-200M pixel/sec

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Silicon Summary

- Mitsubishi 16M DRAM process
- Test silicon works
- Samples available later this year
- Area

~10% Video Output ~12% Pixel ALU ~8% L1\$ The rest is DRAM and L2\$